

## OptiMOS™3 Power-Transistor

### Features

- Optimized for dc-dc conversion
- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Halogen-free according to IEC61249-2-21



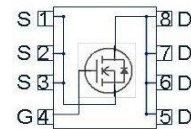
### Product Summary

|                  |      |    |
|------------------|------|----|
| $V_{DS}$         | 200  | V  |
| $R_{DS(on),max}$ | 90   | mΩ |
| $I_D$            | 15.2 | A  |

PG-TSDSON-8



| Type           | Package     | Marking |
|----------------|-------------|---------|
| BSZ900N20NS3 G | PG-TSDSON-8 | 900N20N |



**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol            | Conditions                                | Value       | Unit  |
|-------------------------------------|-------------------|-------------------------------------------|-------------|-------|
| Continuous drain current            | $I_D$             | $T_C=25\text{ °C}$                        | 15.2        | A     |
|                                     |                   | $T_C=100\text{ °C}$                       | 10.7        |       |
|                                     |                   | $T_C=25\text{ °C}$                        | 61          |       |
| Pulsed drain current <sup>2)</sup>  | $I_{D,pulse}$     | $T_C=25\text{ °C}$                        | 61          |       |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=7.6\text{ A}$ , $R_{GS}=25\text{ Ω}$ | 100         | mJ    |
| Reverse diode $dv/dt$               | $dv/dt$           |                                           | 10          | kV/μs |
| Gate source voltage                 | $V_{GS}$          |                                           | ±20         | V     |
| Power dissipation                   | $P_{tot}$         | $T_C=25\text{ °C}$                        | 62.5        | W     |
| Operating and storage temperature   | $T_j$ , $T_{stg}$ |                                           | -55 ... 150 | °C    |
| IEC climatic category; DIN IEC 68-1 |                   |                                           | 55/150/56   |       |

<sup>1)</sup>J-STD20 and JESD22

<sup>2)</sup> see figure 3

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                        |            |                                              |   |   |     |     |
|----------------------------------------|------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case    | $R_{thJC}$ |                                              | - | - | 2.5 | K/W |
| Thermal resistance, junction - ambient | $R_{thJA}$ | 6 cm <sup>2</sup> cooling area <sup>3)</sup> | - | - | 60  |     |

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |                                                             |     |     |     |               |
|----------------------------------|---------------|-------------------------------------------------------------|-----|-----|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                        | 200 | -   | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=30\text{ }\mu\text{A}$                  | 2   | 3   | 4   |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=160\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$  | -   | 0.1 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=160\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$ | -   | 10  | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                     | -   | 1   | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=7.6\text{ A}$                      | -   | 77  | 90  | m $\Omega$    |
| Gate resistance                  | $R_G$         |                                                             | -   | 2.2 | -   | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=7.6\text{ A}$            | 8   | 16  | -   | S             |

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |                                                                                              |   |     |     |    |
|------------------------------|--------------|----------------------------------------------------------------------------------------------|---|-----|-----|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$<br>$f=1\text{ MHz}$                                | - | 690 | 920 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                              | - | 52  | 69  |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                              | - | 5.2 | -   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=100\text{ V},$<br>$V_{GS}=10\text{ V}, I_D=7.6\text{ A},$<br>$R_G=1.6\text{ }\Omega$ | - | 5   | -   | ns |
| Rise time                    | $t_r$        |                                                                                              | - | 4   | -   |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                              | - | 10  | -   |    |
| Fall time                    | $t_f$        |                                                                                              | - | 3   | -   |    |

**Gate Charge Characteristics<sup>4)</sup>**

|                       |               |                                                                              |   |     |      |    |
|-----------------------|---------------|------------------------------------------------------------------------------|---|-----|------|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=100\text{ V}, I_D=7.6\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 3.1 | -    | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                              | - | 1.3 | -    |    |
| Switching charge      | $Q_{sw}$      |                                                                              | - | 2.3 | -    |    |
| Gate charge total     | $Q_g$         |                                                                              | - | 8.7 | 11.6 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                              | - | 4.5 | -    | V  |
| Output charge         | $Q_{oss}$     | $V_{DD}=100\text{ V}, V_{GS}=0\text{ V}$                                     | - | 20  | 26   | nC |

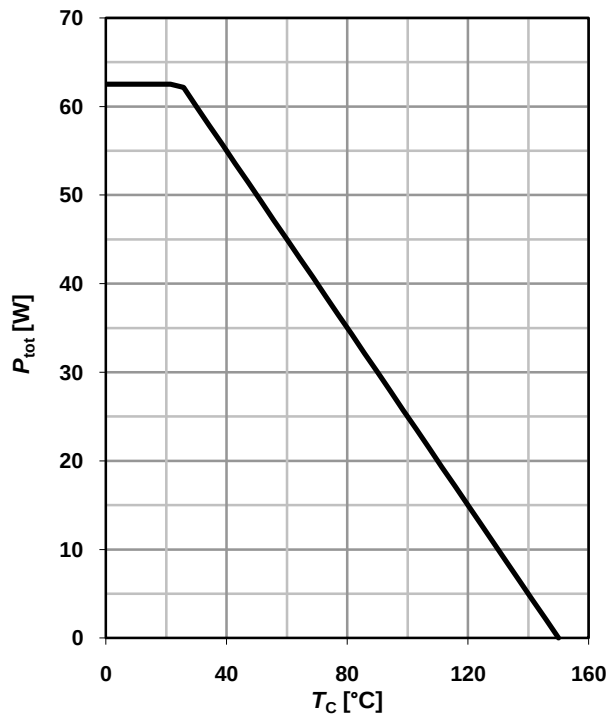
**Reverse Diode**

|                                  |               |                                                                           |   |     |      |    |
|----------------------------------|---------------|---------------------------------------------------------------------------|---|-----|------|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$                                            | - | -   | 15.2 | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                           | - | -   | 61   |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=15.2\text{ A},$<br>$T_J=25\text{ }^\circ\text{C}$ | - | 1   | 1.2  | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=100\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$        | - | 86  | -    | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                           | - | 309 | -    | nC |

<sup>4)</sup> See figure 16 for gate charge parameter definition

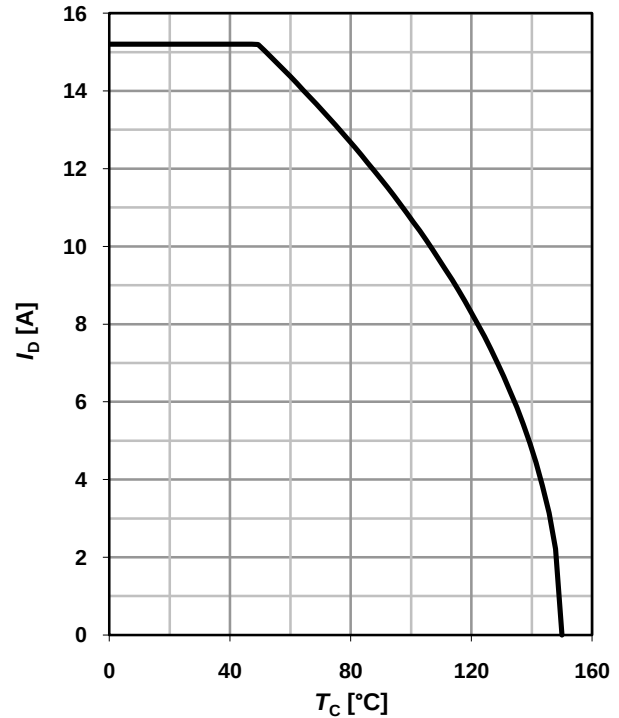
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

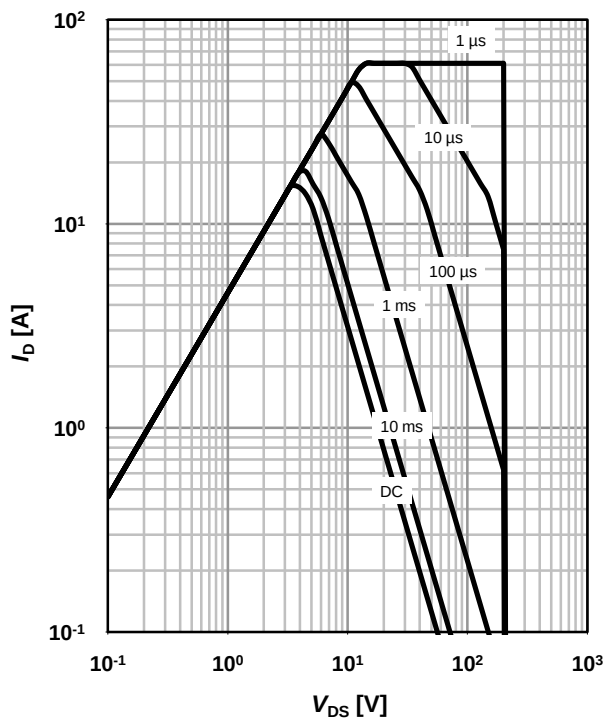
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

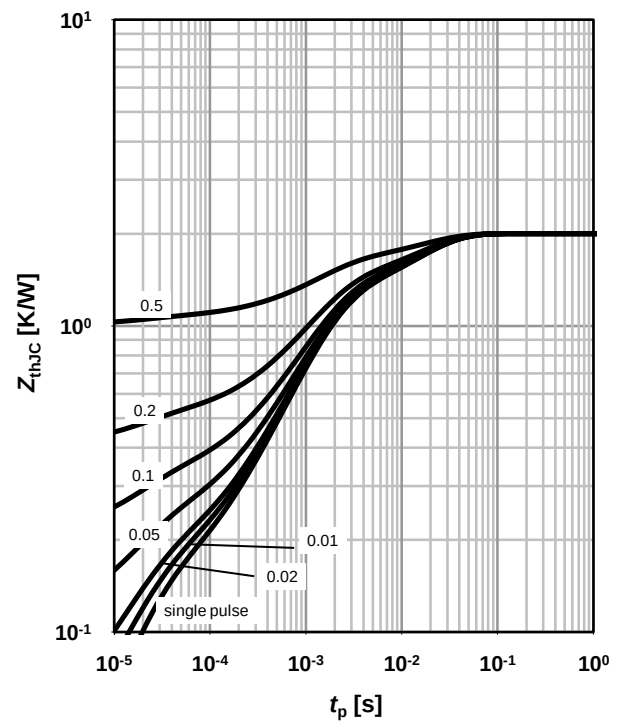
parameter:  $t_p$



### 4 Max. transient thermal impedance

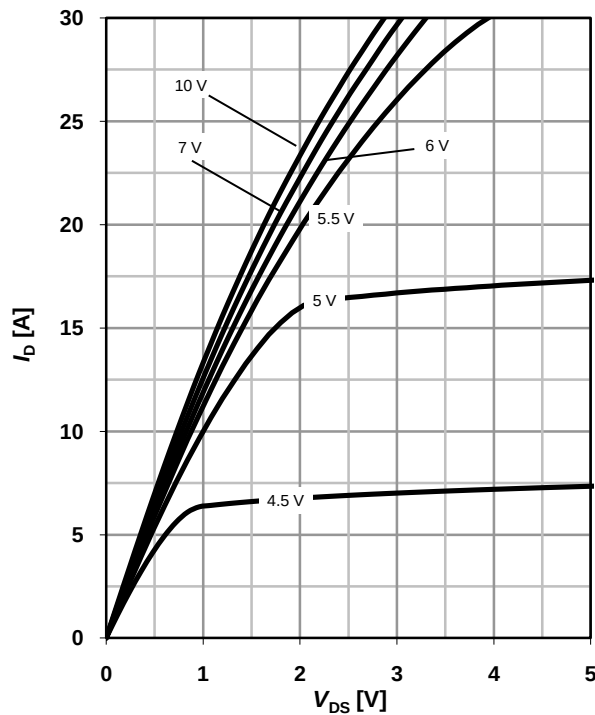
$$Z_{\text{thJC}} = f(t_p)$$

parameter:  $D = t_p/T$



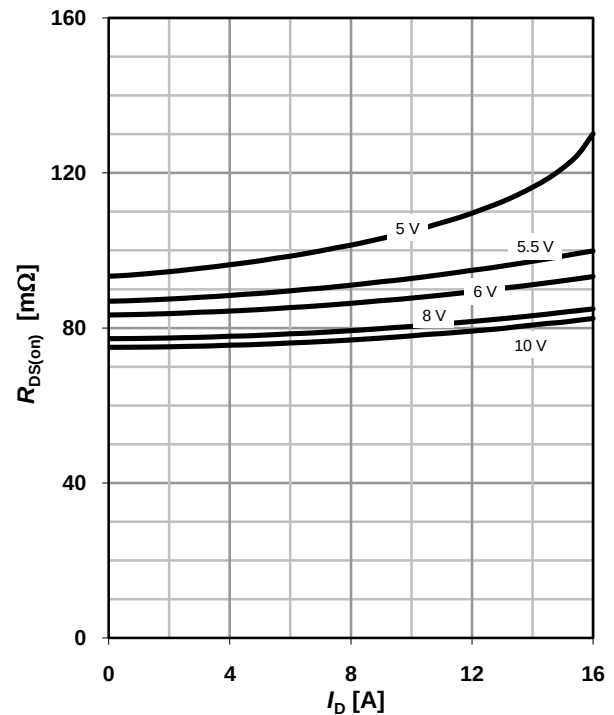
### 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$ 

parameter:  $V_{GS}$ 


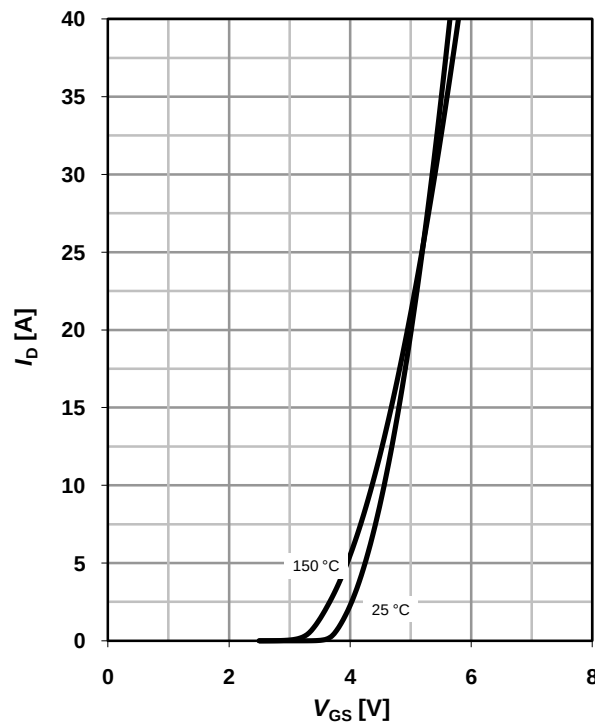
### 6 Typ. drain-source on resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$ 

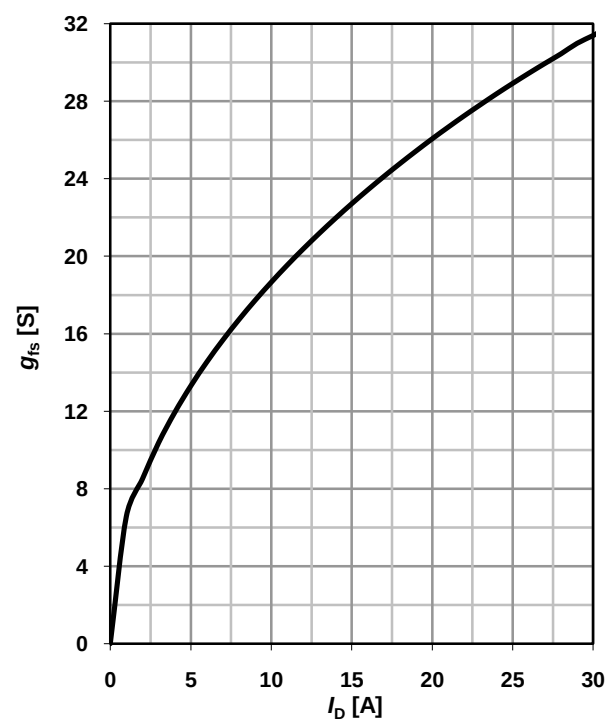
parameter:  $V_{GS}$ 


### 7 Typ. transfer characteristics

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D| R_{DS(on)max}$ 

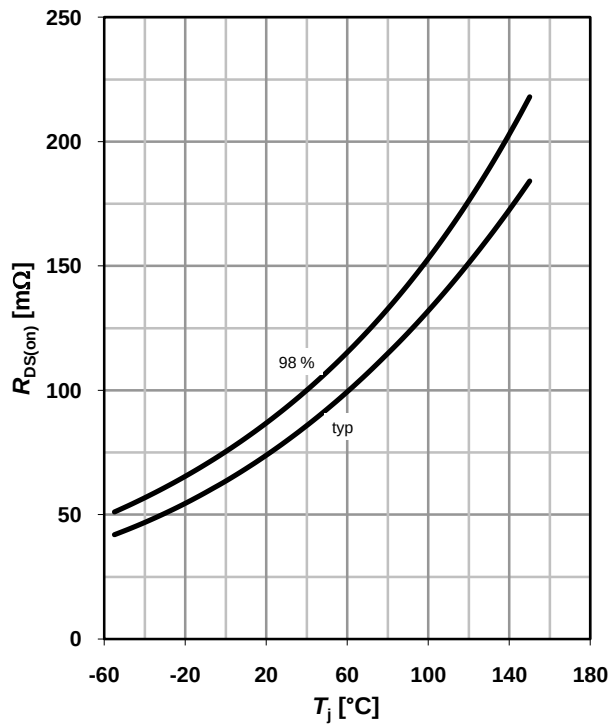
parameter:  $T_j$ 


### 8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$ 


## 9 Drain-source on-state resistance

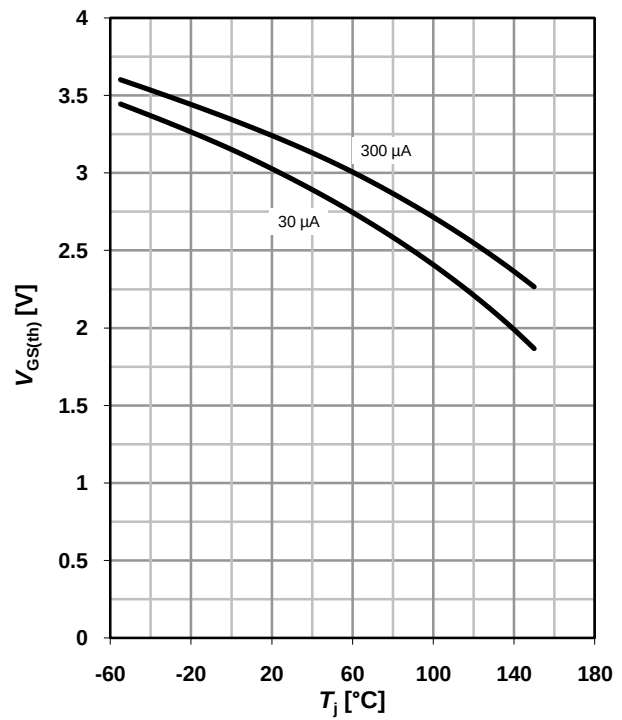
$$R_{DS(on)} = f(T_j); I_D = 7.6 \text{ A}; V_{GS} = 10 \text{ V}$$



## 10 Typ. gate threshold voltage

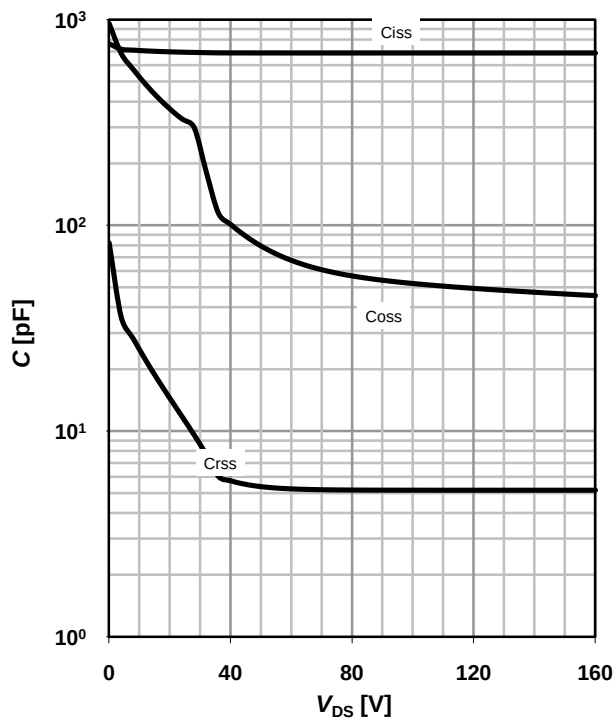
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



## 11 Typ. capacitances

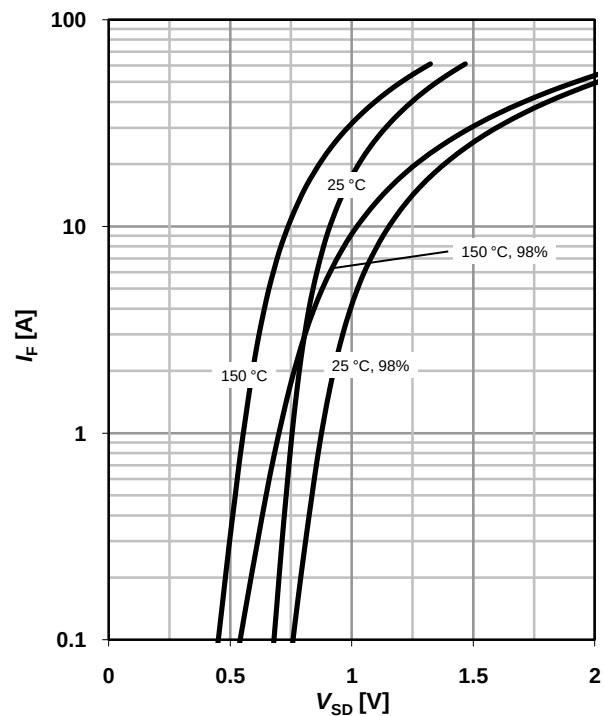
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



## 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

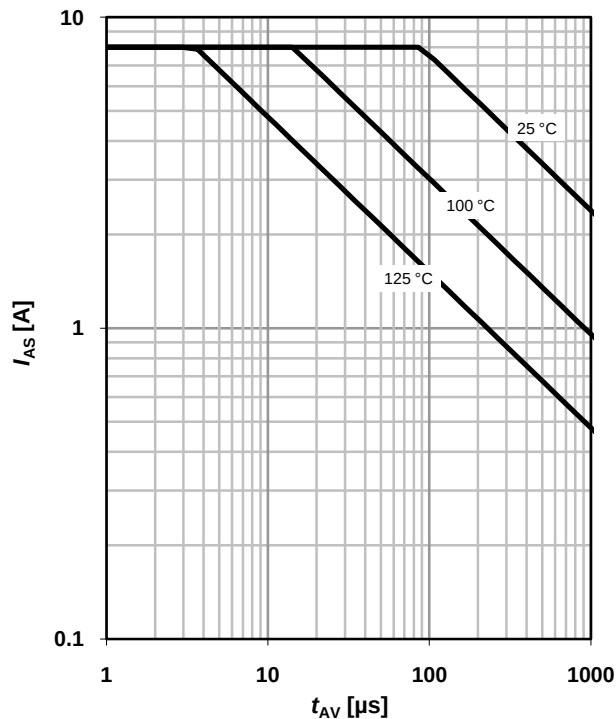
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

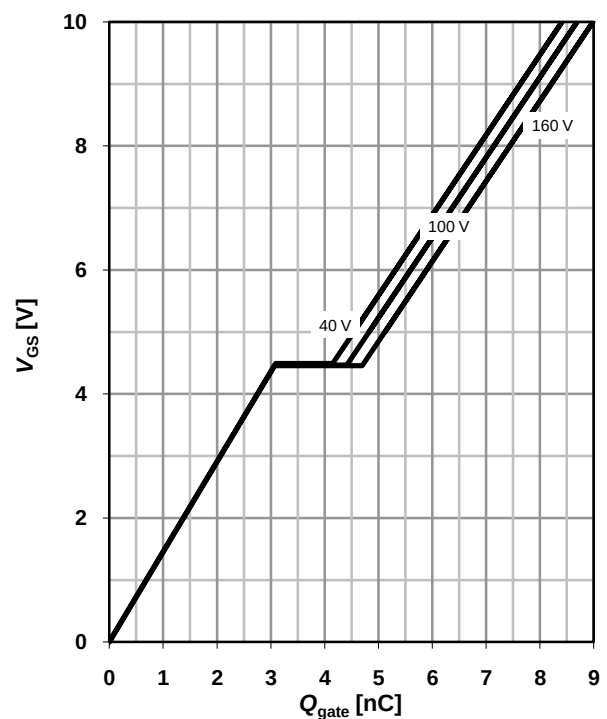
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

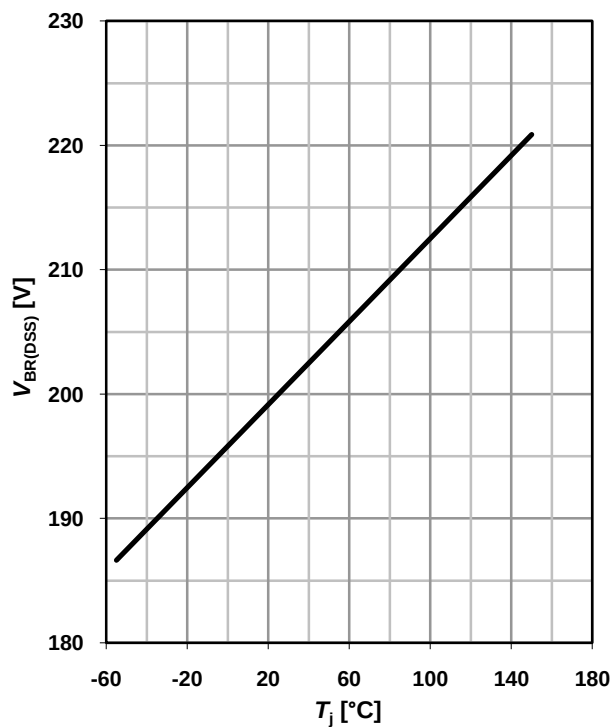
$$V_{GS}=f(Q_{\text{gate}}); I_D=7.6\ \text{A pulsed}$$

parameter:  $V_{DD}$

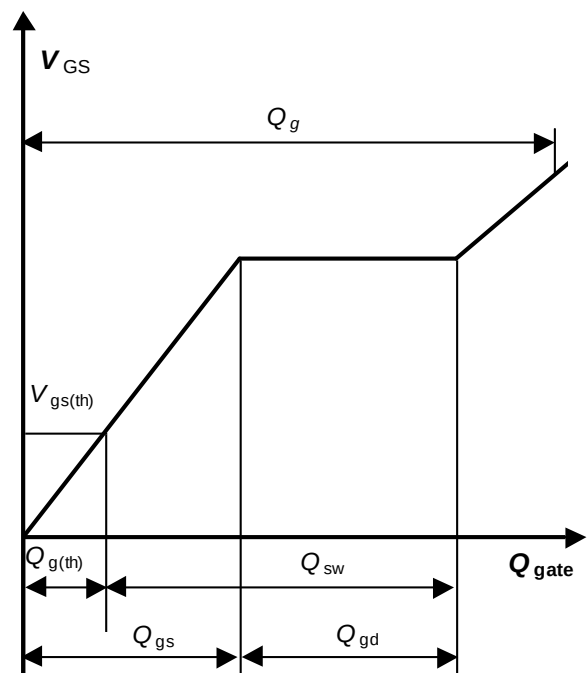


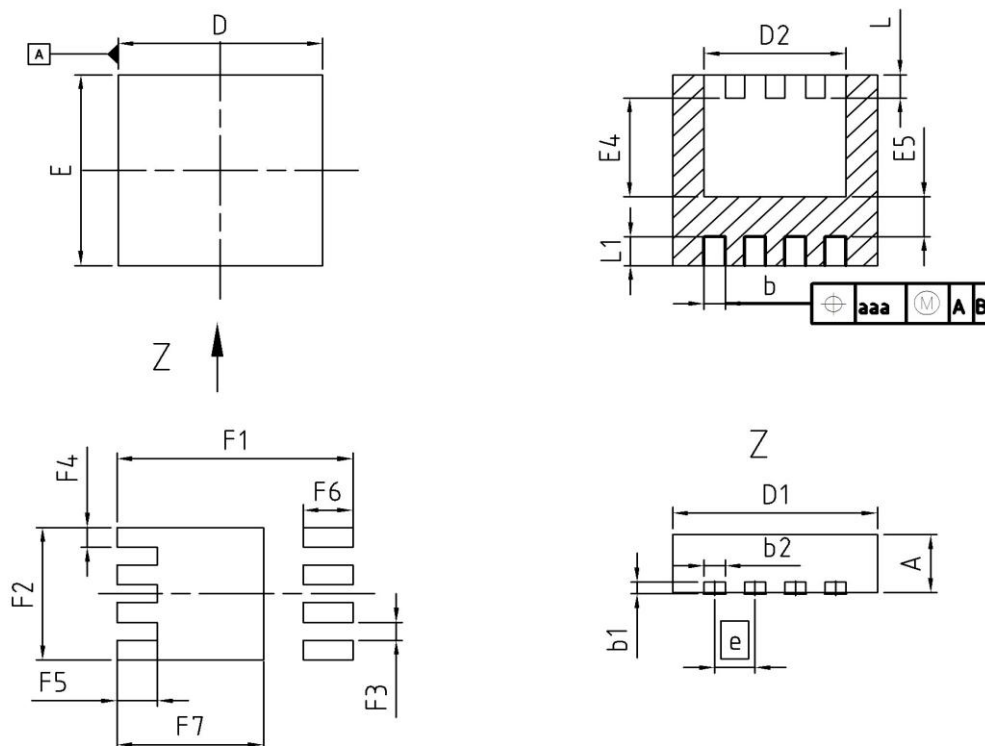
### 15 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$

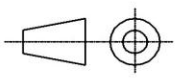


### 16 Gate charge waveforms



**Package Outline:PG-TSDSON-8**


| DIM  | MILLIMETERS |      | INCHES |       |
|------|-------------|------|--------|-------|
|      | MIN         | MAX  | MIN    | MAX   |
| A    | 0.90        | 1.10 | 0.035  | 0.043 |
| b    | 0.24        | 0.44 | 0.009  | 0.017 |
| b1   | 0.10        | 0.30 | 0.004  | 0.012 |
| b2   | 0.20        | 0.44 | 0.008  | 0.017 |
| D=D1 | 3.20        | 3.40 | 0.126  | 0.134 |
| D2   | 2.15        | 2.45 | 0.085  | 0.096 |
| E    | 3.20        | 3.40 | 0.126  | 0.134 |
| E4   | 1.60        | 1.81 | 0.063  | 0.071 |
| E5   | 0.59        | 0.86 | 0.023  | 0.034 |
| e    | 0.65        |      | 0.026  |       |
| N    | 8           |      | 8      |       |
| L    | 0.30        | 0.56 | 0.012  | 0.022 |
| L1   | 0.33        | 0.60 | 0.013  | 0.024 |
| aaa  | 0.25        |      | 0.010  |       |
| F1   | 3.80        |      | 0.150  |       |
| F2   | 2.29        |      | 0.090  |       |
| F3   | 0.31        |      | 0.012  |       |
| F4   | 0.34        |      | 0.013  |       |
| F5   | 0.65        |      | 0.026  |       |
| F6   | 0.80        |      | 0.031  |       |
| F7   | 2.36        |      | 0.093  |       |

|                                                                                                              |
|--------------------------------------------------------------------------------------------------------------|
| DOCUMENT NO.<br>Z8B00131645                                                                                  |
| SCALE<br>0 2.5 5mm                                                                                           |
| EUROPEAN PROJECTION<br> |
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